

A cross-sectional view of a semiconductor device. The device consists of a substrate 101 with a patterned layer 102. A series of rectangular features 106 are formed in the substrate. A layer 108 is deposited on top of the features 106, and a layer 109 is deposited on top of the layer 108. A layer 112 is also shown on the right side of the device.

FIG. 4J

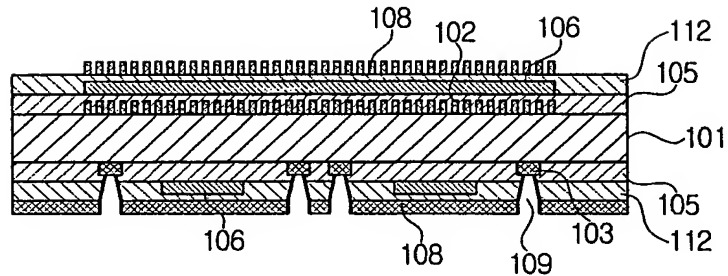


FIG. 4K

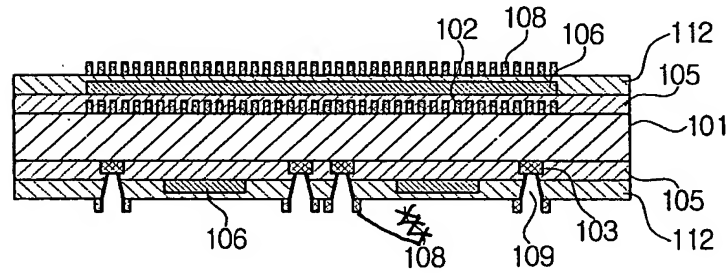


FIG. 4L

